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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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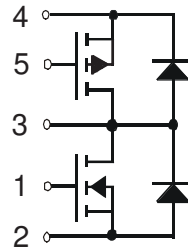
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# Polar™ P & N-Channel Power MOSFETs Common Drain Topology

## FMP36-015P



	P CH.	N CH.
$V_{DSS}$	- 150V	150V
$I_{D25}$	- 22A	36A
$R_{DS(on)}$	110mΩ	40mΩ
$t_{rr(typ)}$	228ns	150ns

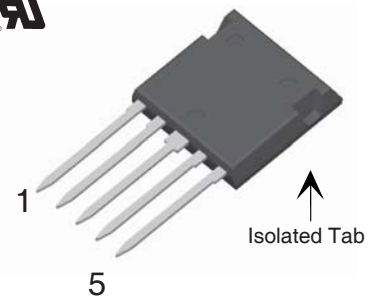
Symbol	Test Conditions	Maximum Ratings
$T_J$		- 55 ... +150 °C
$T_{JM}$		150 °C
$T_{stg}$		- 55 ... +150 °C
$T_L$	1.6mm (0.062 in.) from case for 10s	300 °C
$V_{ISOL}$	50/60HZ, RMS, t=1s, leads-to-tab	2500 V~
$F_C$	Mounting force	20..120 / 4.5..27 N/lb.

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$C_p$	Coupling capacitance between shorted pins and mounting tab in the case		40	pF
$d_S, d_A$	pin - pin	1.7		mm
$d_S, d_A$	pin - backside metal	5.5		mm
Weight		9		g

### P - CHANNEL

Symbol	Test Conditions	Maximum Ratings
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	-150 V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$	-150 V
$V_{GSS}$	Continuous	$\pm 20$ V
$V_{GSM}$	Transient	$\pm 30$ V
$I_{D25}$	$T_C = 25^\circ\text{C}$	- 22 A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	- 90 A
$I_A$	$T_C = 25^\circ\text{C}$	- 36 A
$E_{AS}$	$T_C = 25^\circ\text{C}$	1.5 J
$P_D$	$T_C = 25^\circ\text{C}$	125 W

### ISOPLUS i4-Pak™



### Features

- Silicon chip on Direct-Copper Bond (DCB) substrate
  - UL recognized package
  - Isolated mounting surface
  - 2500V electrical isolation
- Avalanche rated
- Low  $Q_G$
- Low Drain-to-Tab capacitance
- Low package inductance

### Advantages

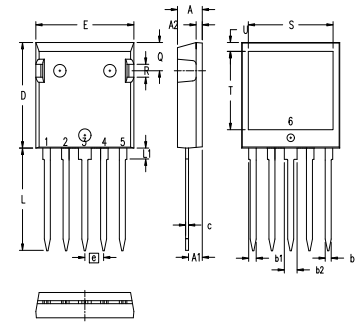
- Low gate drive requirement
- High power density
- Low drain to ground capacitance
- Fast switching

### Applications

- DC and AC motor drives
- Class AB audio amplifiers
- Multi-phase DC to DC converters
- Industrial battery chargers
- Switching power supplies

Symbol	Test Conditions <sup>2</sup> ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V, I_D = -250 \mu A$	-150		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-2.5		-4.5 V
$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			-10 $\mu A$ -250 $\mu A$
$R_{DS(on)}$	$V_{GS} = -10V, I_D = -18A$ , Note 1			110 m $\Omega$
$g_{fs}$	$V_{DS} = -10V, I_D = -18A$ , Note 1	11	19	S
$C_{iss}$	$V_{GS} = 0V, V_{DS} = -25V, f = 1\text{MHz}$		3100	pF
$C_{oss}$			610	pF
$C_{rss}$			100	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = -10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = -18A$ $R_G = 3.3\Omega$ (External)		21	ns
$t_r$			31	ns
$t_{d(off)}$			36	ns
$t_f$			15	ns
$Q_{g(on)}$	$V_{GS} = -10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = -18A$		55	nC
$Q_{gs}$			20	nC
$Q_{gd}$			18	nC
$R_{thJC}$				1.0 $^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

## ISOPLUS i4-Pak™ Outline



NOTE: Bottom heatsink meets 3000 Volts AC 1 sec isolation to the other pins.

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.085	1.17	2.16
b	.045	.055	1.14	1.40
b1	.058	.068	1.47	1.73
b2	.100	.110	2.54	2.79
C	.020	.029	0.51	0.74
D	.819	.840	20.80	21.34
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
L	.780	.840	19.81	21.34
L1	.083	.102	2.11	2.59
Q	.210	.244	5.33	6.20
R	.100	.180	2.54	4.57
S	.660	.690	16.76	17.53
T	.590	.620	14.99	15.75
U	.065	.080	1.65	2.03

Ref: IXYS CO 0077 R0

## Drain-Source Diode

Symbol	Test Conditions <sup>2</sup>	Characteristic Values ( $T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0V$			-22 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			-140 A
$V_{SD}$	$I_F = -18A, V_{GS} = 0V$ , Note 1			-3.3 V
$t_{rr}$	$I_F = -18A, di/dt = 100 A/\mu s$		228	ns
$Q_{RM}$	$V_R = -75V, V_{GS} = 0V$		2.0	$\mu C$
$I_{RM}$		-17.6		A

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**N - CHANNEL**

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^{\circ}\text{C}$ to $150^{\circ}\text{C}$	150	V
$V_{DGR}$	$T_J = 25^{\circ}\text{C}$ to $150^{\circ}\text{C}$ ; $R_{GS} = 1\text{M}\Omega$	150	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^{\circ}\text{C}$	36	A
$I_{DM}$	$T_C = 25^{\circ}\text{C}$ , pulse width limited by $T_{JM}$	150	A
$I_A$	$T_C = 25^{\circ}\text{C}$	50	A
$E_{AS}$	$T_C = 25^{\circ}\text{C}$	1.0	J
$P_D$	$T_C = 25^{\circ}\text{C}$	125	W

Symbol	Test Conditions <sup>2</sup> ( $T_J = 25^{\circ}\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0\text{V}$ , $I_D = 250\text{ }\mu\text{A}$	150		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{V}$			$\pm 100\text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0\text{V}$ $T_J = 150^{\circ}\text{C}$			25 $\mu\text{A}$ 250 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10\text{V}$ , $I_D = 31\text{A}$ , (Note 1)		33	40 $\text{m}\Omega$
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 31\text{A}$ , (Note 1)	14	24	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		2250	pF
$C_{oss}$			660	pF
$C_{rss}$			185	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 31\text{A}$ $R_G = 10\Omega$ (External)		27	ns
$t_r$			38	ns
$t_{d(off)}$			76	ns
$t_f$			35	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 31\text{A}$		70	nC
$Q_{gs}$			20	nC
$Q_{gd}$			38	nC
$R_{thJC}$				1.0 $^{\circ}\text{C/W}$
$R_{thCS}$		0.15		$^{\circ}\text{C/W}$



**Source-Drain Diode**
**Characteristic Values**
 $T_J = 25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Test Conditions <sup>3</sup>	Min.	Typ.	Max.
$I_S$	$V_{GS} = 0V$			36 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			150 A
$V_{SD}$	$I_F = 62A$ , $V_{GS} = 0V$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25A$ , $-di/dt = 100A/\mu s$ $V_R = 100V$ , $V_{GS} = 0V$		150	ns
$Q_{RM}$				
			2.0	$\mu C$

Note 1: Pulse test,  $t \leq 300\mu s$ , duty cycle,  $d \leq 2\%$ .

**ADVANCE TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated objective result. IXYS reserves the right